S3154

Silicon Epitaxial Planar Type

Diode

T-03-09

TENTATIVE

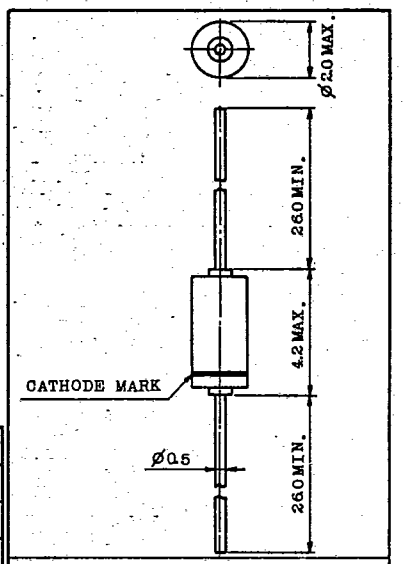
COMMUNICATION AND INDUSTRIAL APPLICATIONS.

HIGH VOLTAGE, ULTRA HIGH SPEED SWITCHING APPLICATIONS.

FEATURES:

- Low Forward Voltage : V_F=1.2V (Max.)
- Small Total Capacitance : C_T=2pF (Max.)
- Fast Reverse Recovery Time : t_{rr}=50ns (Max.)
- Hermetically Sealded Miniature Glass Package.

Unit in mm



JEDEC	DO-35
EIAJ	SC-40
TOSHIBA	1-2A1A

Weight : 0.14g

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (peak) Reverse Voltage	V_{RM}	300	V
Reverse Voltage	V_R	250	V
Maximum (Peak) Forward Current	I_{FM}	600	mA
Average Forward Current	I_O	200	mA
Surge Current (10ms)	I_{FSM}	2	A
Power Dissipation	P	400	mW
Junction Temperature	Tj	175	°C
Storage Temperature Range	Tstg	-65~175	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	I_F=10mA	-	0.75	1.0	V
	$V_{F(2)}$	I_F=100mA	-	0.95	1.2	V
Reverse Current	$I_{R(1)}$	V_R=150V	-	-	100	nA
	$I_{R(2)}$	V_R=250V	-	-	0.2	μA
Total Capacitance	C_T	V_R=0, f=1MHz	-	0.9	2.0	pF
Reverse Recovery Time	t_{rr}	V_R=6V, I_F=10mA, R_L=100Ω	-	30	50	ns